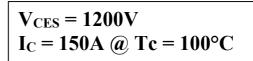
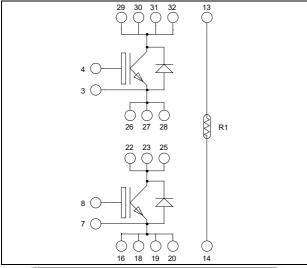


Phase leg Trench + Field Stop IGBT3 Power Module





Pins 29/30/31/32 must be shorted together
Pins 26/27/28/22/23/25 must be shorted together
to achieve a phase leg
Pins 16/18/19/20 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings (a) $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		1200	V
$I_{\rm C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
	Continuous Conector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	150	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation	$T_C = 25$ °C	833	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	300A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics	(Per IGBT)
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Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.7	2.1	17
	Confector Emitter Saturation Voltage	$I_{\rm C} = 150 A$ $T_{\rm j} = 125 ^{\circ} {\rm C}$		2.0		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Condition	ıs	Min	Тур	Max	Unit	
Cies	Input Capacitance	$\begin{aligned} V_{GE} &= 0V \\ V_{CE} &= 25V \\ f &= 1MHz \end{aligned}$			10.7			
C_{oes}	Output Capacitance				0.56		nF	
C_{res}	Reverse Transfer Capacitance				0.48			
Q_{G}	Gate charge	V_{GE} = ±15V; V_{CE} =600V I_{C} =150A			1.4		μС	
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			280			
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			40		ns	
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$			420			
T_{f}	Fall Time	$R_G = 2.2\Omega$			75			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)			290			
T_{r}	Rise Time	$V_{GE} = \pm 15V$			45			
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$			520		ns	
T_{f}	Fall Time	$R_G = 2.2\Omega$			90			
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		14		mJ	
E_{off}	Turn-off Switching Energy	$I_C = 150A$ $R_G = 2.2\Omega$		$T_j = 125$ °C		16		1113
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; V_{E} $t_{p} \le 10\mu s$; $T_{j} =$			600		A	
R_{thJC}	Junction to Case Thermal Resistance					0.15	°C/W	

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic Test Conditions		Min	Typ	Max	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$				350	μA
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		150		A
N/	Diede Ferryand Veltage	$I_F = 150A$	$T_j = 25^{\circ}C$		1.6	2.1	V
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_i = 125$ °C		1.6		V
4	, D. D. T.	$T_j = 25$ °C		170			
t_{rr}	Reverse Recovery Time		$T_j = 125$ °C		280		ns
0	Daviana Dagavani Changa	$I_F = 150A$ $V_R = 600V$	$T_j = 25$ °C		14		
Qrr	Reverse Recovery Charge	$di/dt = 2500 \text{ A/\mu s}$	$T_j = 125$ °C		28		μС
E_{r}	Reverse Recovery Energy		$T_j = 25$ °C		6		mJ
\mathbf{E}_{r}	Reverse Recovery Energy		$T_j = 125$ °C		11		1113
R_{thJC}	Junction to Case Thermal Resistance					0.25	°C/W



Thermal and package characteristics

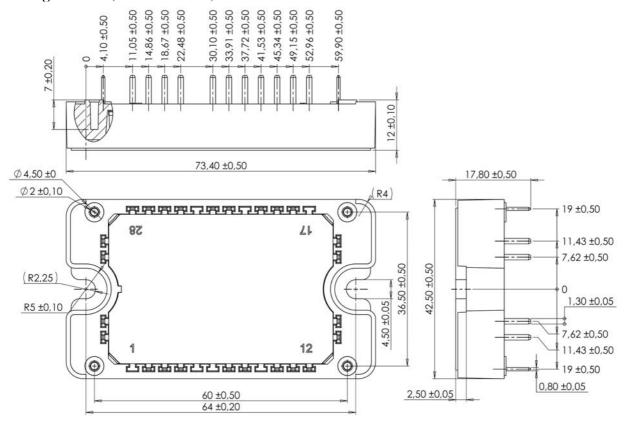
Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz					V
$T_{\rm J}$	Operating junction temperature range			-40	150	
T_{JOP}	Recommended junction temperature under switch	Recommended junction temperature under switching conditions			T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	gg

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	ee @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \begin{array}{l} \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T} \end{array}$$

Package outline (dimensions in mm)

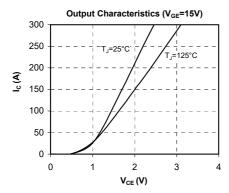


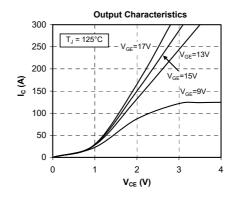
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

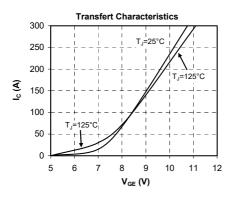
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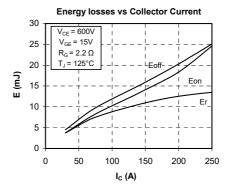


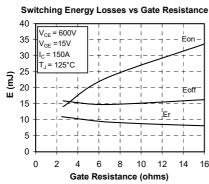
Typical Performance Curve

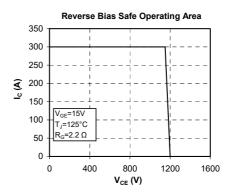


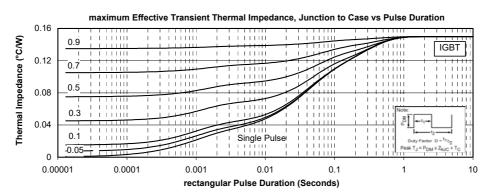




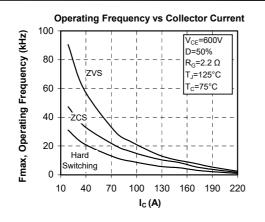


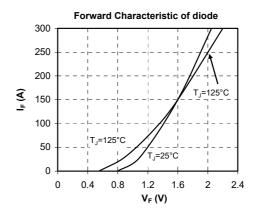


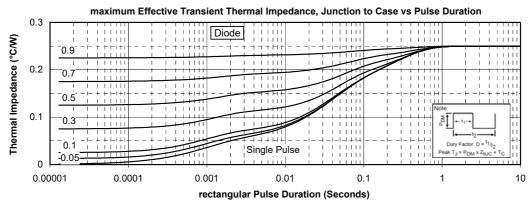














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